



BSKE160T120

General Description

概述

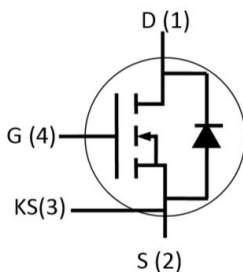
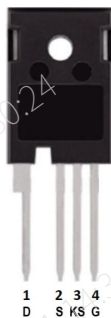
Specifically designed for Automotive applications, this SiC Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per unit area.

本产品是一款专为汽车应用设计的碳化硅功率MOSFET产品，采用了先进的工艺技术，产品的单位面积导通电阻非常低。

Features

特点

- High Speed Switching with Low Capacitances
开关速度快，寄生电容小
- High Blocking Voltage with Low $R_{DS(on)}$
阻断电压高，开通电阻低
- 100% avalanche tested
100%通过雪崩测试
- Halogen Free and RoHS Compliant
无卤元素，符合 RoHS



Typical Applications

典型应用

- Solar Inverters
太阳能逆变器
- EV motor drive
EV 电机驱动
- High Voltage DC/DC Converters
高压 DC/DC 变压器
- Switched mode power supplies
开关模式电源

Ordering Information

订货信息

Type 型号	$BV_{DSS}[V]$ 漏极-源极电压	$R_{DS(on)}[m\Omega]$ 导通电阻	$T_{jmax}[^{\circ}C]$ 最高结温	Marking 标记	Packing 封装外形
BSKE160T120	1200	160	175	160T120	TO247-4L



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Maximum Rated Values

最大额定参数

Parameter 参数	Symbol 符号	Value 数值	Unit 单位
Drain-Source Voltage, $T_j \geq 25^\circ\text{C}$ 漏-源电压, $T_j \geq 25^\circ\text{C}$	V_{DSS}	1200	V
Drain Current(continuous)at $T_c=25^\circ\text{C}$ 常温下漏极电流(持续)	I_{D}	22	A
Drain Current(continuous)at $T_c=100^\circ\text{C}$ $T_c=100^\circ\text{C}$ 下漏极电流(持续)		15	
Pulsed Drain current, tp limited by $T_{j \max}$ 集电极脉冲电流, 脉宽时间受 $T_{j \max}$ 限制	I_{DM}	38	
Gate-Source Voltage 栅极-源极电压	V_{GSmax}	-10/+22	V
Gate-Source Voltage (Recommended operational values) 栅极-源极电压(推荐工作电压)	V_{GSop}	-5/+18	V
Power Dissipation $T_c = 25^\circ\text{C}$ 常温耗散功率	P_{D}	112	W
Storage Temperature Range 储存温度范围	T_{stg}	-55 to +175	$^\circ\text{C}$
Operating junction temperature Range 工作结温	T_{J}		
Solder Temperature, 1.6mm case from for10s 焊接温度	T_{L}		
Mounting Torque 安装力矩	M_{d}	1 8.8	Nm lbf-in

Caution: These values must not be exceeded under any conditions.

注意：任何条件下都不能超出上述值。

Thermal Resistance

热阻

Parameter 参数	Symbol 符号	Value 值	Unit 单位
Thermal Resistance, Junction to Case, Max. 结-管壳热阻	$R_{\theta\text{JC}}$	1.33	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient, Max. 结-环境热阻	$R_{\theta\text{JA}}$	30	

**BSKE160T120****Electrical Characteristic at $T_j = 25^\circ\text{C}$ (unless otherwise specified)** **$T_j=25^\circ\text{C}$ 时电学特性（除非特别声明）**

Parameter 参数	Symbol 符号	Conditions 条件	Value 值			Unit 单位
			Min. 最小 值	Typ. 典型 值	Max. 最大 值	
Static Characteristic 静态特性						
Drain to Source Breakdown Voltage 漏极-源极击穿电压	BV _{DSS}	V _{GS} =0V, I _D =100μA T _j =25°C	1200	-	-	V
Zero Gate Voltage Drain Current 栅源-漏极漏电流	I _{DSS}	V _{DS} =1200V, V _{GS} =0V T _j =25°C	-	-	100	μA
Gate to Body Leakage Current 栅极-源极漏电流	I _{GSS}	V _{GS} =18V, V _{DS} =0V	-	-	100	nA
Gate to Body Leakage Current 栅极-源极漏电流	I _{SGS}	V _{GS} =-10V, V _{DS} =0V	-	-	100	nA
Static Drain-source On Resistance 漏极-源极开通电阻	R _{DS(on)}	V _{GS} =18V, I _D =10A T _j =25°C	-	105	130	mΩ
		V _{GS} =18V, I _D =10A T _j =175°C	-	185	-	
Forward Transconductance 跨导	g _{FS}	V _{DS} =20V, I _D =10A T _j =25°C	-	7	-	S
Gate Threshold Voltage 栅极-源极阈值电压	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =2.5mA T _j =25°C	2.2	3.4	4.2	V
		V _{DS} =V _{GS} , I _{DS} =2.5mA T _j =175°C	-	2.4	-	
Gate Resistance 栅极电阻	R _G	f=1MHz	-	4.5	-	Ω
Dynamic Characteristic 动态特性						
Input Capacitance 输入电容	C _{iss}	V _{DS} =1000V, f=1MHz, V _{GS} =0V	-	1850	-	pF
Output Capacitance 输出电容	C _{oss}		-	80	-	
Reverse Transfer Capacitance 反向传输电容	C _{rss}		-	15	-	
Total Gate Charge 栅极总电荷	Q _{g(tot)}	V _{DD} =800V, I _D =10A, V _{GS} =-5/18V	-	45	-	nC
Gate-source Charge 栅-源电荷	Q _{gs}		-	12	-	
Gate-drain Charge 栅-漏电荷	Q _{gd}		-	10	-	



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Switching Characteristic at $T_j=25^\circ\text{C}$ (Inductive Load)

$T_j=25^\circ\text{C}$ 时开关特性（电感负载）

Parameter 参数	Symbol 符号	Conditions 条件	Value 值			Unit 单位
			Min. 最小值	Typ. 典型值	Max. 最大值	
MOSFET Characteristic MOSFET 特性						
Turn-on delay time 开通延迟时间	t _{d(on)}	V _{DS} =800V, V _{GS} =-5/18V, I _D =10A, R _{G(ext)} =5Ω, L=500μH	-	15	-	ns
Rise time 上升时间	t _r		-	28	-	
Turn-off delay time 关断延迟时间	t _{d(off)}		-	41	-	
Fall time 下降时间	t _f		-	37	-	
Turn-on Switching Energy 开通损耗	Eon	V _{DS} =800V, V _{GS} =-5/18V, I _D =10A, R _{G(ext)} =5Ω, L=500μH	-	0.08	-	mJ
Turn-off Switching Energy 关断损耗	Eoff		-	0.37	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

源极-漏极二极管特性

Source to Drain Diode Forward Voltage 源极-漏极正向电压	V_{SD}	$V_{GS}=-5\text{V},$ $I_{SD}=5\text{A},$ $T_j=25^\circ\text{C}$	-	3.2	-	V
		$V_{GS}=-5\text{V},$ $I_{SD}=5\text{A},$ $T_j=175^\circ\text{C}$	-	2.9	-	
Continuous Diode Forward Current 正向电流	I_S	$T_C=25^\circ\text{C}$	-	-	30	A
Reverse recovery time 反向恢复时间	t_{rr}	$T_j=25^\circ\text{C},$ $V_{GS}=-5\text{V}/18\text{V},$ $V_R=800\text{V},$ $I_{SD}=10\text{A},$ $diF/dt=400\text{A/us}$	-	28	-	ns
Recovered charge 恢复电荷	Q_{rr}		-	46	-	nC
Peak reverse recovery current 反向峰值电流	I_{rrm}		-	2.8	-	A

Notes:

a: Repetitive Rating : Pulse width limited by maximum junction temperature

b: Essentially independent of operating temperature

注:

a: 重复范围：脉冲宽度受限于最大结温

b: 本质上与工作温度无关



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Electrical characteristics diagram 特性曲线

Figure 1. Output Characteristics $T_J = -55^\circ\text{C}$

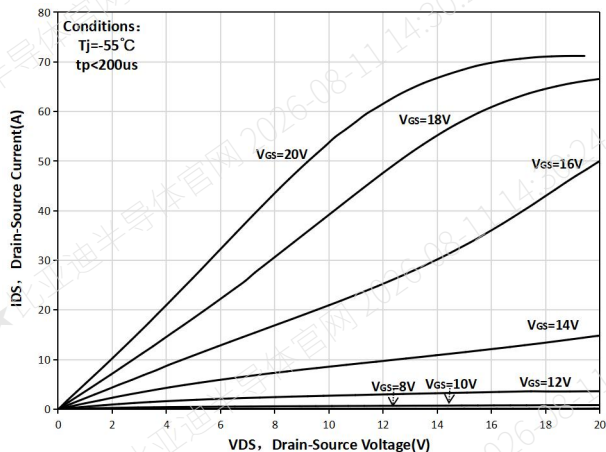


Figure 2. Output Characteristics $T_J = 25^\circ\text{C}$

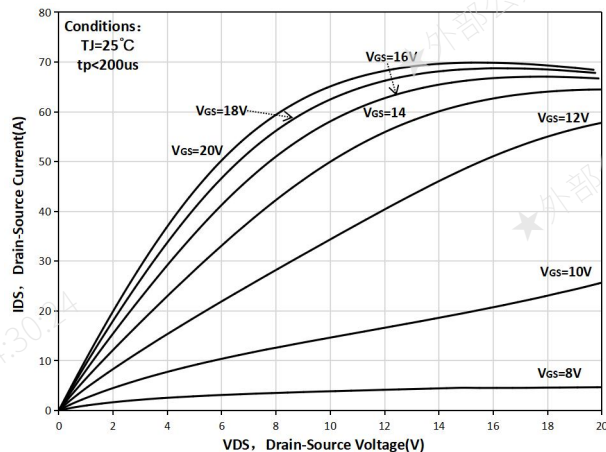


Figure 3. Output Characteristics $T_J = 175^\circ\text{C}$

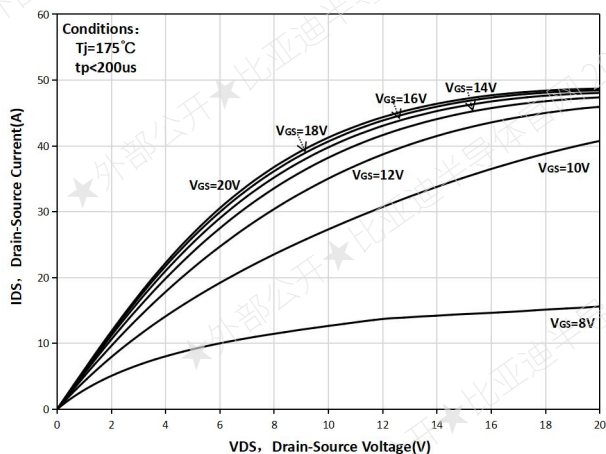


Figure 4. On-Resistance For Various Gate Voltage

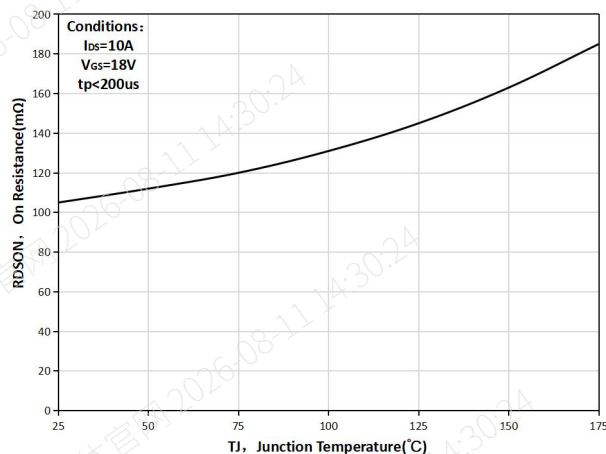


Figure 5. Transfer Characteristic
for Various Junction Temperatures

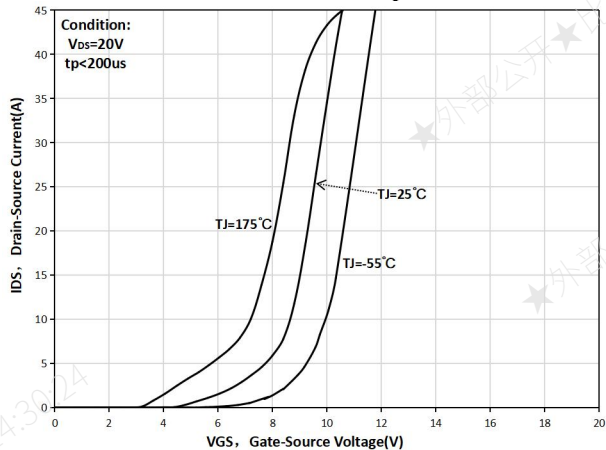


Figure 6. Threshold Voltage vs. Temperature

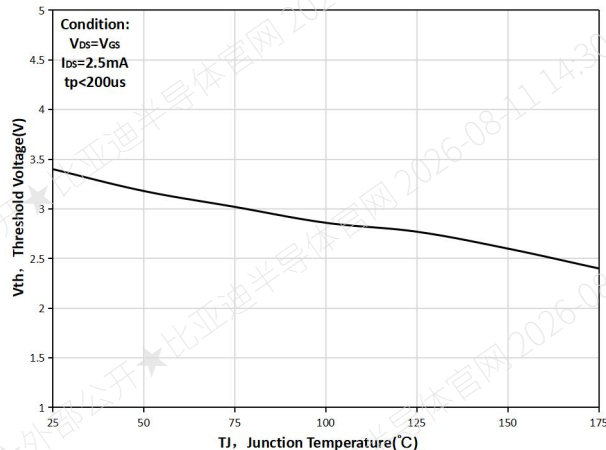


Figure 7. Body Diode Characteristics at -55°C

Figure 8. Body Diode Characteristics at 25°C



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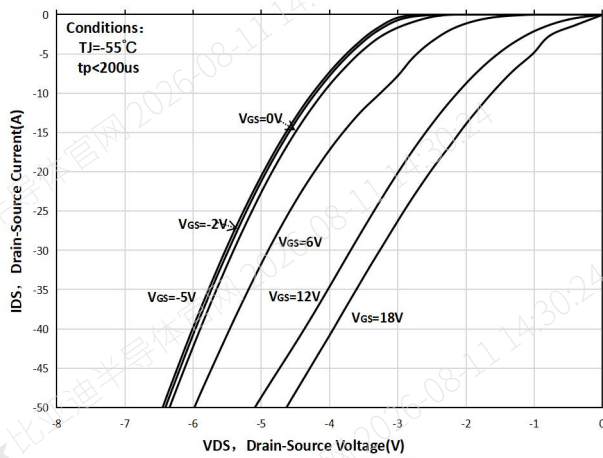


Figure 9. Body Diode Characteristics at 175°C

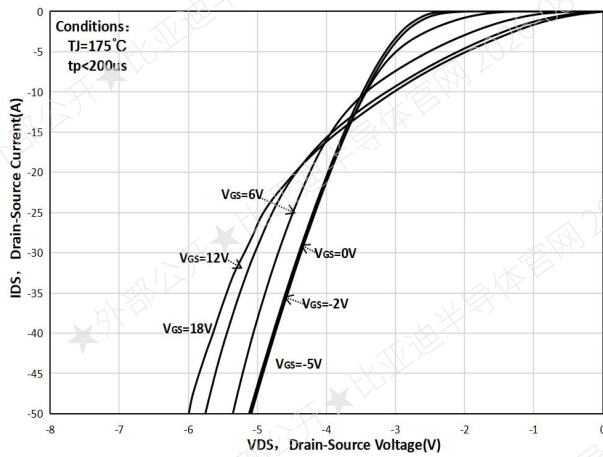


Figure 10. Capacitances vs. Drain-Source Voltage

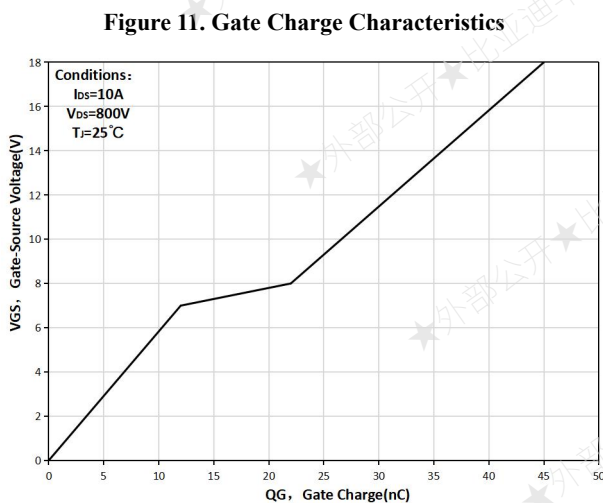


Figure 11. Gate Charge Characteristics

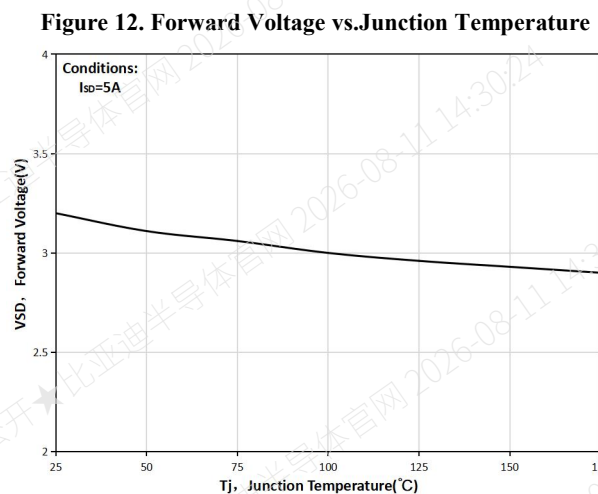


Figure 12. Forward Voltage vs. Junction Temperature

Figure 13. Body Diode Characteristics for Various Junction Temperatures

Figure 14. Clamped Inductive Switching Energy Vs. Temperature



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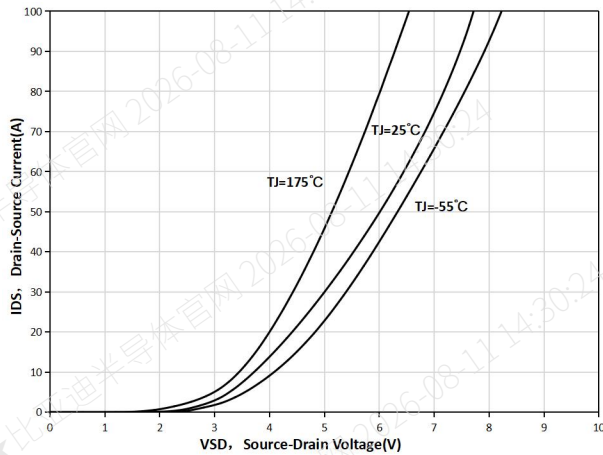


Figure 15. Switching Times vs. Junction Temperature

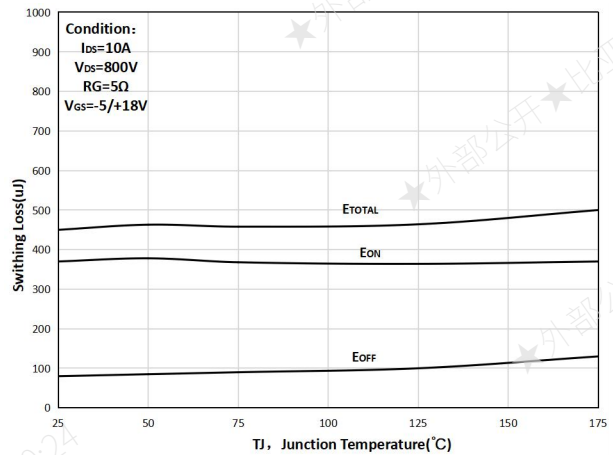


Figure 16. On-Resistance vs. Drain Current

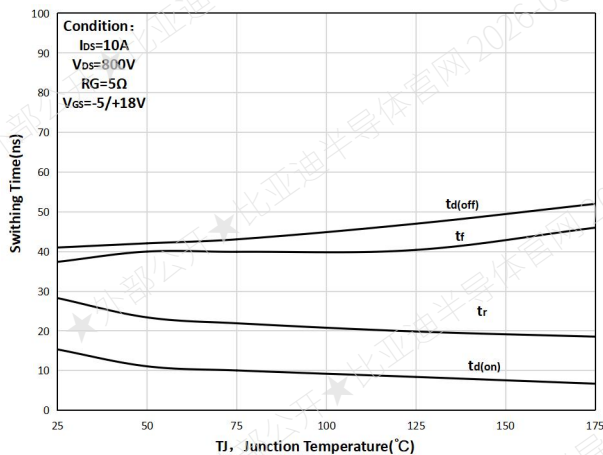


Figure 17. Power Dissipation Derating

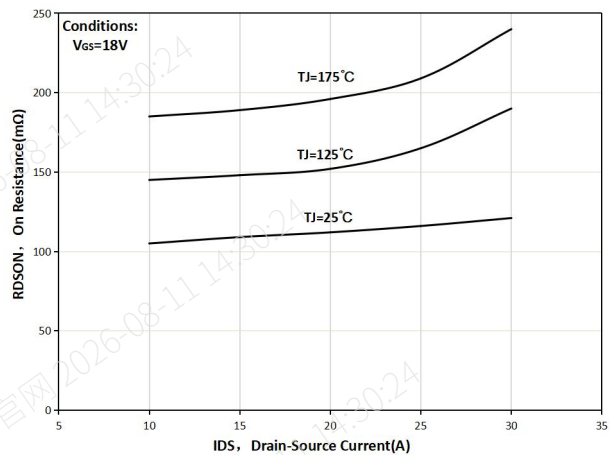
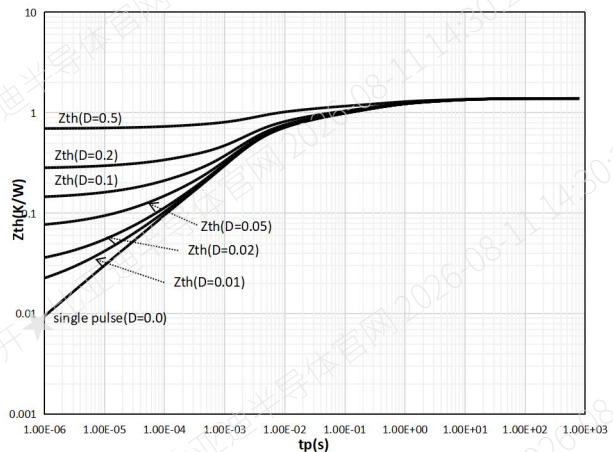
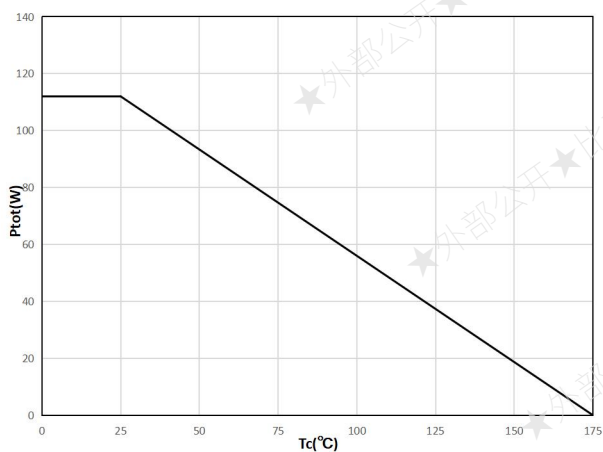


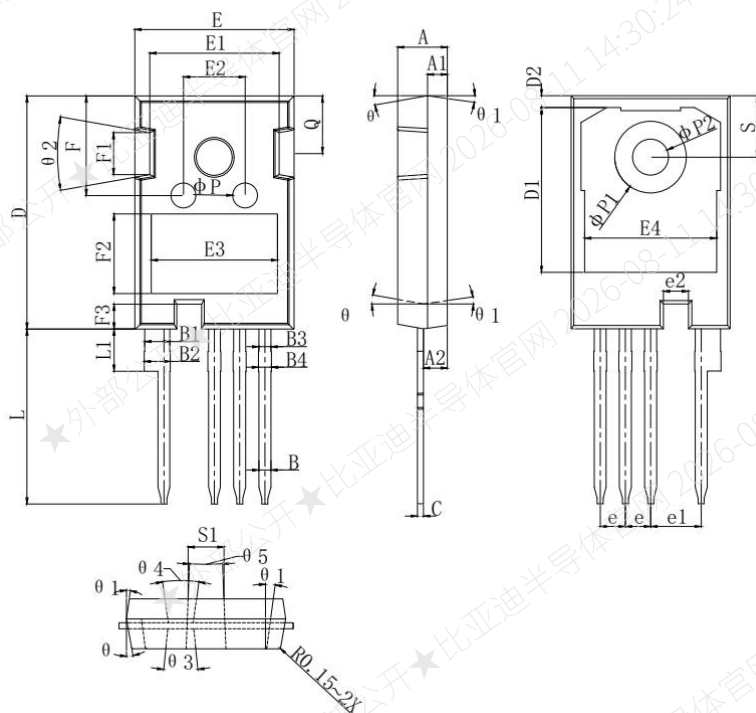
Figure 18 Transient Thermal Impedance





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TO247-4L Packing Outline Dimensions: TO247-4L 封装外形尺寸



Dim.	Mechanical Dimensions /mm	
	MIN	MAX
A	4.83	5.21
A1	1.9	2.16
B	1.07	1.33
B2	2.39	2.94
B4	1.07	1.6
C	0.55	0.68
D	23.25	23.65
D1	16.35	16.75
E	15.74	16.14
E4	13.06	13.46
F1	3.68	5.1
F3	2.35	2.65
e	2.34	2.74
e1	4.88	5.28
L	17.31	17.82
L1	3.97	4.37
ΦP2	3.50	3.70
S	6.05	6.27
Q	5.49	6.00

Note: The mold may vary little from different packaging plants, please refer to the actual product.
备注: 因封装厂的模具存在细微差异, 请以实物的尺寸为准

Packing 包装

Package 包装	Pcs/tube 片/管	Tube/ inner box 管/内盒	Inner box/ carton 内盒/外箱	Pcs/carton 片/外箱
Tube 管	30	12	6	2160



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- **Warranty Period:** Unless otherwise agreed in the COOPERATION AGREEMENT or other WRITTEN DOCUMENTS, the Warranty Period for products specified in this specification shall be one year from the date of purchase if the products are properly preserved.

Special instructions: Storage Temperature: $20\pm 5^{\circ}\text{C}$; Relative Humidity: 30%-60%; The product should be stored in a place away from direct light and vibration.

质保期: 除双方在合作协议或其他书面文件中另行约定外, 产品妥当保存的情况下自购买之日起, 本规格书所述产品质保期为一年。

特殊说明: 储存温度: $20\pm 5^{\circ}\text{C}$; 相对湿度: 30%-60%; 产品应放置于避光地方, 避免震动。

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